# RENESAS

## RJP30H2DPK-M0

Silicon N Channel IGBT High speed power switching

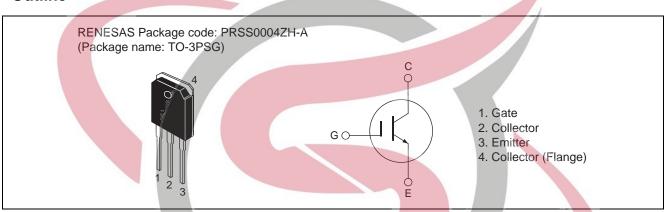
R07DS0467EJ0200 Rev.2.00 Jun 15, 2011

Datasheet

### Features

- Trench gate and thin wafer technology (G6H-II series)
- Low collector to emitter saturation voltage:  $V_{CE(sat)} = 1.4 V \text{ typ}$
- High speed switching:  $t_f = 100$  ns typ,  $t_f = 180$  ns typ
- Low leak current:  $I_{CES} = 1 \ \mu A \ max$

### Outline



## **Absolute Maximum Ratings**

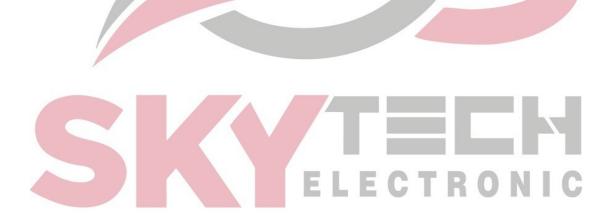
 $(Ta = 25^{\circ}C)$ 

			(1a - 25C)
Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V <sub>CES</sub>	360	V
Gate to Emitter voltage	V <sub>GES</sub>	±30	V
Collector current	lc	35	А
Collector peak current	ic(peak) Note1	250	А
Collector dissipation	Pc Note2	60	W
Junction to case thermal impedance	өј-с	2.08	°C/W
Junction temperature	Тј	150	O°-
Storage temperature	Tstg	–55 to +150	°C
Notes: 1. $PW \le 10 \ \mu s$ , duty cycle $\le 1\%$ 2. $Tc = 25^{\circ}C$	ELEC	TRO	NIC

## **Electrical Characteristics**

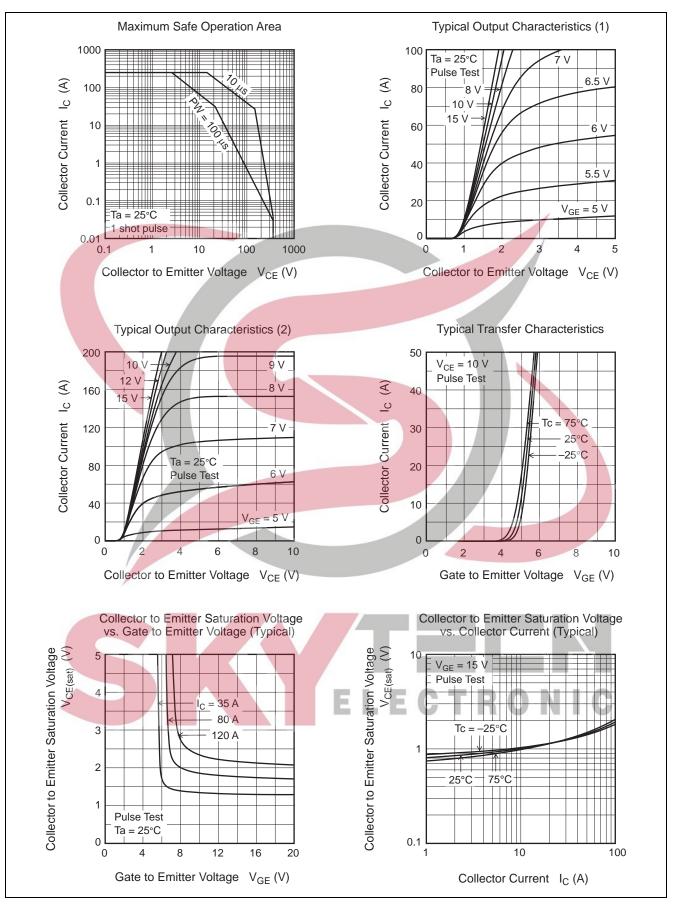
						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I <sub>CES</sub>	_	—	1	μΑ	$V_{CE} = 360 \text{ V}, \text{ V}_{GE} = 0$
Gate to emitter leak current	I <sub>GES</sub>	_	—	±100	nA	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	V <sub>GE(off)</sub>	2.5	—	5	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.4	1.9	V	$I_C = 35 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
Input capacitance	Cies		1200	—	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	60	_	pF	V <sub>GE</sub> = 0
Reveres transfer capacitance	Cres	_	30	_	pF	f = 1 MHz
Total gate charge	Qg	_	37	_	nC	V <sub>GE</sub> = 15 V
Gate to emitter charge	Qge	_	6	_	nC	V <sub>CE</sub> = 150 V
Gate to collector charge	Qgc	_	10	_	nC	I <sub>C</sub> = 35 A
Switching time	t <sub>d(on)</sub>	_	0.02	-	μS	I <sub>C</sub> = 35 A
	tr	_	0.1	-	μS	$R_L = 4.5 \Omega$
	t <sub>d(off)</sub>		0.06	-	μS	V <sub>GE</sub> = 15 V
	t <sub>f</sub>		0.18		μS	$R_{G} = 5 \Omega$

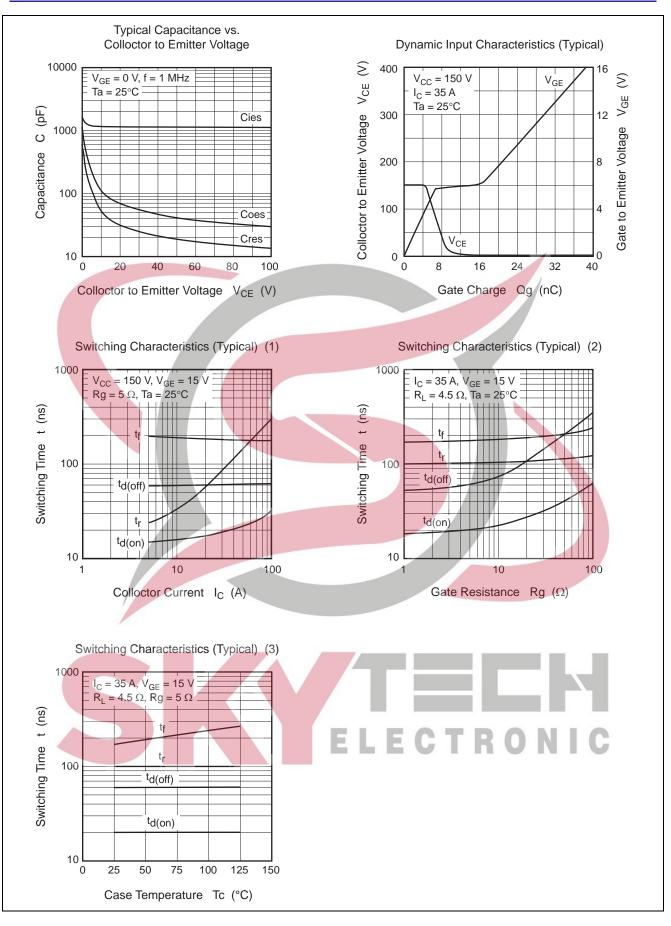
Notes: 3. Pulse test.

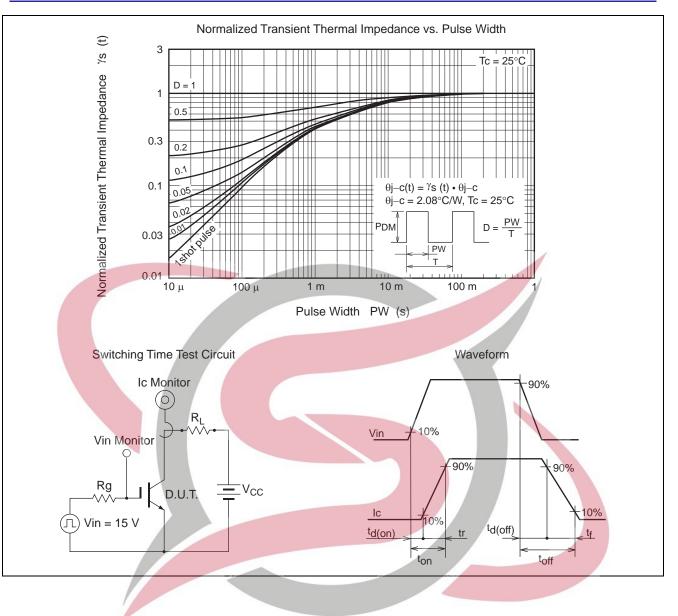


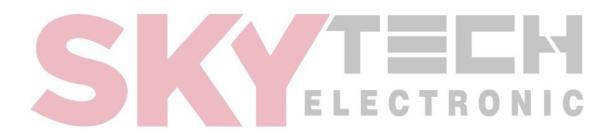
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#### **Main Characteristics**

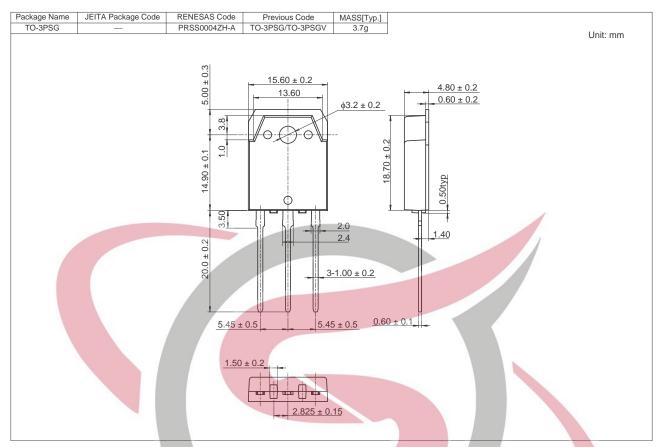








#### **Package Dimension**



#### **Ordering Information**

Orderable Part Number	Quantity	Shipping Container	
RJP30H2DPK-M0-T2	360 pcs	Box (Tube)	





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